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AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application. Claim 1 has been amended and claim 26 has been newly added. In response to the Notice of Non-Compliant Amendment under 37 C.F.R.1.121, the text of withdrawn claims 21-24 is included herein.

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**Listing of Claims:**

1. (Currently amended) A system that measures an etch of a mask feature, comprising:
  - one or more mask creating ~~fabricating~~ components that fabricate one or more features on an alternating aperture phase shift mask;
  - a driving component that controls the one or more mask creating ~~fabricating~~ components;
  - an emitting component that directs light on to at least one of the features on the alternating aperture phase shift mask; and
  - an analysis component that measures one or more feature parameters based on a light reflected and/or refracted from the one or more features, the measured feature parameter utilized by the driving system to control the ~~fabrication~~ mask creating component during fabrication process and post-fabrication process in an alternating aperture phase shift mask.
2. (Original) The system of claim 1, comprising a processor operatively coupled to the measuring system and the fabricating component driving system.
3. (Cancelled)
4. (Original) The system of claim 1, the fabricating components are etching components.

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5. (Original) The system of claim 1, the features comprise at least one of an aperture and a grating.
6. (Original) The system of claim 1, the analysis component comprises a scatterometry system for processing the light reflected from the one or more features.
7. (Original) The system of claim 1, the fabricating components are etching components.
8. (Original) The system of claim 1, the features comprise at least one of an aperture and a grating.
9. (Original) The system of claim 1, the processor maps the mask into a plurality of grid blocks and makes a determination of fabrication conditions at the one or more grid blocks.
10. (Original) The system of claim 1, the fabrication conditions comprise at least one of the depth, width and profile of the features.
11. (Original) The system of claim 1, the processor determines the existence of an unacceptable fabrication condition for the one or more features based upon a determined feature signature differing from an acceptable feature signature.
12. (Original) The system of claim 2, the processor controls the one or more fabricating components to regulate fabricating the one or more features on the mask.
13. (Original) The system of claim 1, the features comprise at least one of an aperture and a grating.
14. (Original) The system of claim 1, the fabricating components are etching components.

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15. (Original) A system for monitoring the profile of an aperture on an alternating aperture phase shift mask, the system comprising:
- a system for directing light onto an alternating aperture phase shift mask; and
  - a measuring system for measuring one or more aperture parameters based on a light reflected from the aperture.
16. (Original) The system of claim 15, the aperture parameters comprise at least one of aperture depth, aperture width and aperture wall slope.
17. (Original) The system of claim 15, comprising a processor adapted to receive aperture data from the measuring system and to facilitate determining whether the alternating aperture phase shift mask has been fabricated within one or more pre-determined tolerances.
18. (Original) The system of claim 17, the pre-determined tolerances comprise at least one of aperture depth, aperture width and aperture wall slope.
19. (Original) The system of claim 15, the measuring system comprises a scatterometry system for processing the light reflected from an aperture to determine an aperture signature.
20. (Original) The system of claim 15, the processor determines whether the mask has been fabricated within one or more pre-determined tolerances based upon a determined aperture signature differing from an acceptable aperture signature.

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21. (Withdrawn) A method for monitoring and controlling aperture etching in an alternating aperture phase shift mask, comprising:

- etching one or more apertures on the alternating aperture phase shift mask;
- directing light onto at least one of the one or more apertures;
- collecting light reflected from the at least one aperture;
- employing scatterometry to analyze the reflected light to determine at least one of the depth, shape, location, profile and width of the at least one aperture; and
- selectively controlling the etching of the one or more apertures in the mask.

22. (Withdrawn) The method of claim 21 comprising:

- etching one or more gratings on the alternating aperture phase shift mask;
- directing light onto at least one of the one or more gratings;
- collecting light reflected from the at least one grating; and
- employing scatterometry to analyze the reflected light to determine at least one of the depth, shape, location, profile and width of the at least one grating.

23. (Withdrawn) A method for determining whether an alternating aperture phase shift mask has been fabricated with desired aperture etching parameters, comprising:

- etching one or more apertures on the alternating aperture phase shift mask;
- directing light onto at least one of the one or more apertures;
- collecting light reflected from the at least one aperture;
- employing scatterometry to analyze the reflected light to determine at least one of the depth, shape, location, profile and width of the at least one aperture; and
- determining the acceptability of the alternating aperture phase shift mask based on at least one of the depth, shape, location, profile and width of the at least one aperture.

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24. (Withdrawn) The method of claim 23 comprising:  
etching one or more gratings on the alternating aperture phase shift mask;  
directing light onto at least one of the one or more gratings;  
collecting light reflected from the at least one grating; and  
employing scatterometry to analyze the reflected light to determine at least one of  
the depth, shape, location, profile and width of the at least one grating.

25. (Original) A system for controlling a process for etching openings in an  
alternating aperture phase shift mask, comprising:

means for sensing at least one of the shape, location, depth, width and opening  
wall slopes of one or more apertures on the alternating aperture phase shift mask;

means for etching one or more apertures on the alternating aperture phase shift  
mask; and

means for selectively controlling the etching of the one or more apertures based  
on analysis of data collected by the means for sensing the shape, location, depth, width  
and opening wall slopes of the one or more apertures.

26. (New) A phase shift mask manufacturing component that fabricates one  
or more features on a phase shift mask, comprising:

a component that directs light on to at least one of the features on the phase shift  
mask;

a processing component receives reflected and/or refracted and measures one or  
more feature parameters based on the light reflected and/or refracted from the one or  
more features; and

a feedback component that utilizes the measurement of the phase shift mask to  
adjust the fabrication process.